

# **3.3V ESD Protection Diodes**

# Ultra Low Capacitance ESD Protection Diode for High Speed Data Line

### **ESDL1531**

The ESDL1531 ESD protection diodes are designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines.

#### **Features**

- Low Capacitance (0.15 pF Typ, I/O to GND)
- Protection for the Following IEC Standards: IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- USB 2.0/3.x
- Thunderbolt
- MHL 2.0
- eSATA

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	74	-55 to +150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)		260	°C
IEC 61000-4-2 Contact IEC 61000-4-2 Air	ESD	±30 ±30	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

See Application Note AND8308/D for further description of survivability specs.

#### MARKING DIAGRAM

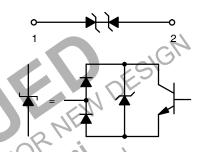


ESDL1531 X4DFN2 (01005) CASE 718AA



J = Device Code M = Date Code

# PIN CONFIGURATION AND SCHEMATIC



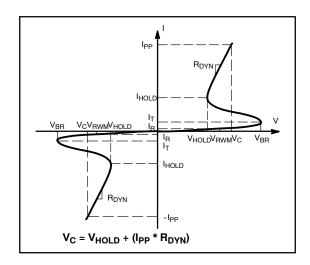
#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

,	,
Symbol	Parameter
V <sub>RWM</sub>	Working Peak Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
V <sub>HOLD</sub>	Holding Reverse Voltage
I <sub>HOLD</sub>	Holding Reverse Current
R <sub>DYN</sub>	Dynamic Resistance
I <sub>PP</sub>	Maximum Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub> V <sub>C</sub> = V <sub>HOLD</sub> + (I <sub>PP</sub> * R <sub>DYN</sub> )



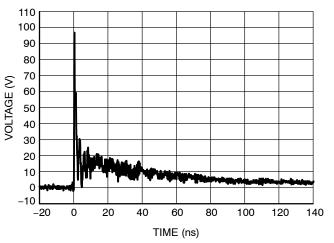
#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	$V_{RWM}$	I/O Pin to GND		$U_{\Delta}$	3.3	٧
Breakdown Voltage	$V_{BR}$	I <sub>T</sub> = 1 mA, I/O Pin to GND	5.5		8.6	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 3.3 V, I/O Pin to GND	K i		1.0	μΑ
Reverse Holding Voltage	V <sub>HOLD</sub>	I/O Pin to GND	cell	2.1		V
Holding Reverse Current	I <sub>HOLD</sub>	I/O Pin to GND	12,10	17		mA
Clamping Voltage TLP (Note 1)	V <sub>C</sub>	$I_{PP} = 8 A$ $\begin{cases} EC 61000-4-2 \text{ Level 2 equivalent} \\ (\pm 4 \text{ kV Contact}, \pm 4 \text{ kV Air}) \end{cases}$	RM	6.5		٧
		$I_{PP} = 16 \text{ A}$   IEC 61000-4-2 Level 2 equivalent (±8 kV Contact, ±15 kV Air)		10.2		
Reverse Peak Pulse Current	I <sub>PP</sub>	IEC61000-4-5 (8/20 μs)	5.7	7.5		Α
Clamping Voltage (8/20 μs)	V <sub>C</sub>	IPP = 5.7 A		5.6	6.5	٧
Dynamic Resistance	R <sub>DYN</sub>	I/O Pin to GND		0.46		Ω
Junction Capacitance	C <sub>J</sub>	$V_R = 0 \text{ V, } f = 1 \text{ MHz}$		0.15	0.3	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions:  $Z_0 = 50 \Omega$ ,  $t_p = 100 \text{ ns}$ ,  $t_r = 1 \text{ ns}$ , averaging window;  $t_1 = 70 \text{ ns}$  to  $t_2 = 90 \text{ ns}$ .

#### **TYPICAL CHARACTERISTICS**



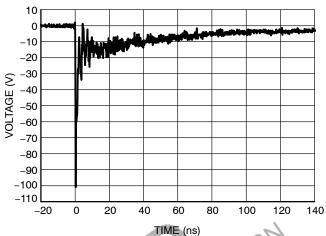
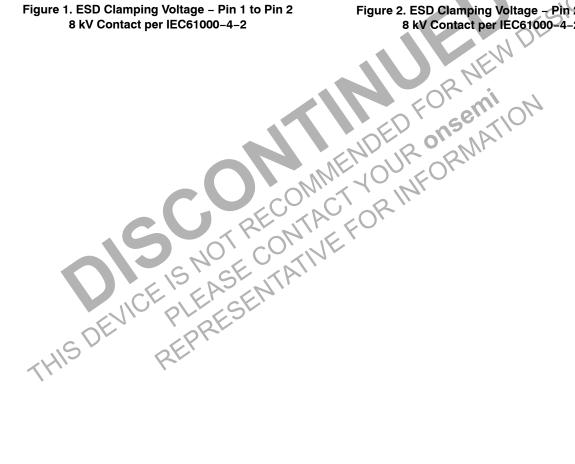
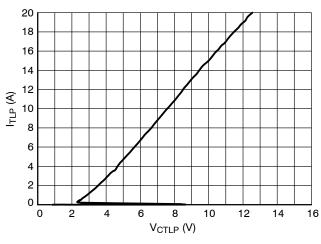


Figure 1. ESD Clamping Voltage - Pin 1 to Pin 2 8 kV Contact per IEC61000-4-2

Figure 2. ESD Clamping Voltage - Pin 2 to Pin 1 8 kV Contact per IEC61000-4-2



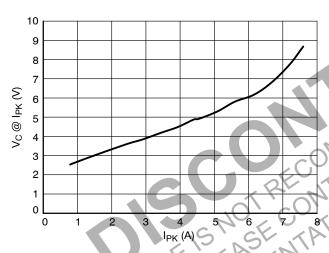
#### **TYPICAL CHARACTERISTICS**



20 18 16 14 12 10 8 6 4 2 0 0 2 4 6 8 10 12 14 16

Figure 3. 100 ns TLP I-V Curve - Pin 1 to Pin 2

Figure 4. 100 ns TLP I–V Curve – Pin 2 to Pin 1



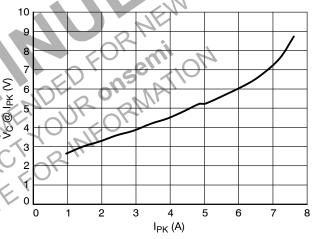


Figure 5. Clamping Voltage vs. Peak Pulse Current – Pin 1 to Pin 2 (t<sub>p</sub> = 8/20 μs)

Figure 6. Clamping Voltage vs. Peak Pulse Current – Pin 2 to Pin 1 ( $t_p$  = 8/20  $\mu$ s)

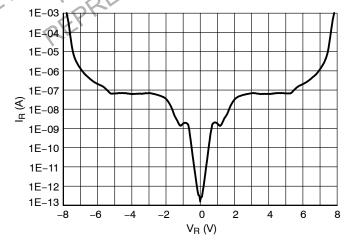
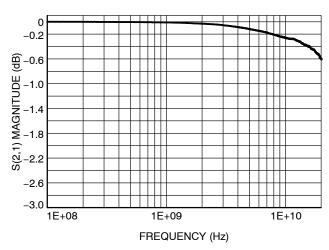


Figure 7. Reverse Leakage Current

#### TYPICAL CHARACTERISTICS



0.40 0.35 0.30 0.25 (Ld 0.20 O 0.15 0.10 0.05 0 1E+10 1E+08 1E+09 FREQUENCY (Hz)

Figure 8. Insertion Loss

Figure 9. Capacitance Over Frequency

#### **ORDERING INFORMATION**

ORDERING INFORMATION		No Mr.
Device	Package	Shipping <sup>†</sup>
ESDL1531MX4T5G	X4DFN2 (Pb-Free)	10,000 / Tape & Reel
†For information on tape and reel specification Specifications Brochure, BRD8011/D.	ns, including part orientation and tape size	s, please refer to our Tape and Reel Packaging

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### IEC 61000-4-2 Spec.

•					
Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)	
1	2	7.5	4	2	
2	4	15	8	4	
3	6	22.5	12	6	
4	8	30	16	8	

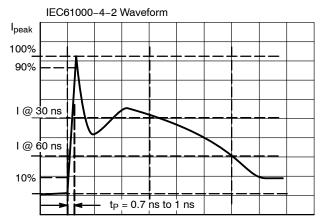


Figure 10. IEC61000-4-2 Spec

#### Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 11. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 12 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

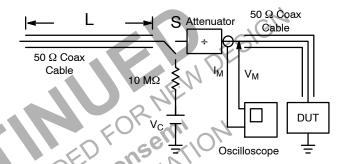


Figure 11. Simplified Schematic of a Typical TLP System

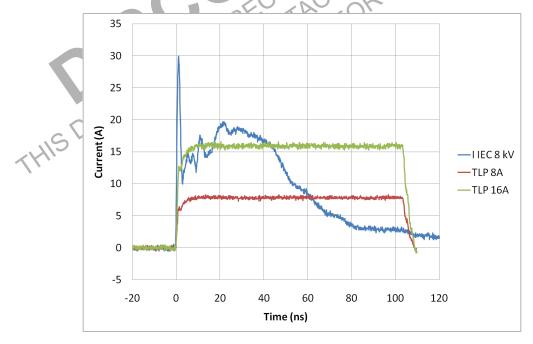


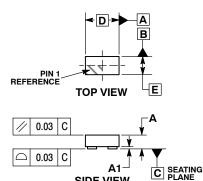
Figure 12. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms



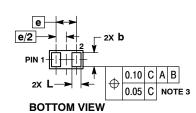
#### X4DFN2, 0.445x0.24, 0.27P CASE 718AA ISSUE A



**DATE 21 MAR 2017** 



SIDE VIEW



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS. EXPOSED COPPER ALLOWED AS SHOWN.

	MILLIMETERS				
DIM	MIN NOM MAX				
Α	0.15	0.18	0.21		
A1			0.03		
b	0.170	0.185	0.200		
D	0.415	0.445	0.475		
E	0.210	0.240	0.270		
е	0.270 BSC				
L	0.105	0.120	0.135		

#### **GENERIC MARKING DIAGRAMS\***

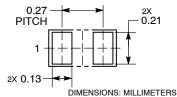




X = Specific Device Code

\*This information is generic. Please refer to device data sheet for actual part marking. Some products may not follow the Generic Marking.

#### **RECOMMENDED MOUNTING FOOTPRINT\***



See Application Note AND8398/D for more mounting details

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	X4DFN2, 0.445X0.24, 0.27F	)	PAGE 1 OF 1	

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